

**METHOD FOR TREATING A SEMICONDUCTOR
MATERIAL FOR SUBSEQUENT BONDING**

ABSTRACT

A method for treating a semiconductor material for subsequent bonding. The technique includes bombarding a surface of the semiconductor material with a beam containing a controlled number of ions in ion clusters. The beam etches a pattern in
5 the surface, and the number of ions is controlled to provide a desired roughness of the surface pattern to improve adhesion during subsequent bonding.

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